

NCEP40T11K

NCE N-Channel Super Trench Power MOSFET



The NCEP40T11K uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

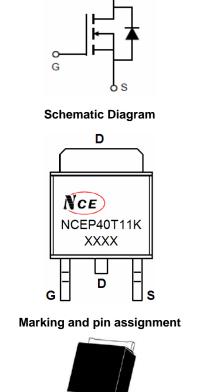
V_{DS} =40V,I_D =110A
R_{DS(ON)}=2.4mΩ (typical) @ V_{GS}=10V
R_{DS(ON)}=3.3mΩ (typical) @ V_{GS}=4.5V

- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 150 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED! 100% ΔVds TESTED!



γD



TO-252 -2L top view

Package Marking and Ordering Information

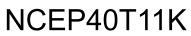
Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP40T11K	NCEP40T11K	TO-252-2L	-	-	-

Absolute Maximum Ratings (T_c=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	40	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous (Silicon Limited)	Ι _D	110	А
Drain Current-Continuous(T _C =100°C)	I _D (100℃)	85	A
Pulsed Drain Current (Package Limited)	I _{DM}	340	А
Maximum Power Dissipation	PD	150	W
Derating factor		1	W/°C
Single pulse avalanche energy (Note 5)	E _{AS}	500	mJ
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C







Thermal Characteristic

Electrical Characteristics (T_C=25 $^{\circ}$ C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	· · ·		•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	40		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.2	1.7	2.2	V
Drain Course On Chate Desistance	P	V _{GS} =10V, I _D =55A	-	2.4	2.8	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =55A	-	3.3	3.9	mΩ
Forward Transconductance	g fs	V _{DS} =5V,I _D =55A	-	60	-	S
Dynamic Characteristics (Note4)	· · ·		•			
Input Capacitance	C _{lss}		-	3510	4200	PF
Output Capacitance	Coss	V _{DS} =20V,V _{GS} =0V, F=1.0MHz	-	860	1000	PF
Reverse Transfer Capacitance	Crss		-	60	78	PF
Switching Characteristics (Note 4)	· · ·		•			
Turn-on Delay Time	t _{d(on)}		-	10.5	-	nS
Turn-on Rise Time	tr	V_{DD} =20V,I _D =55A	-	4	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =1.6 Ω	-	35	-	nS
Turn-Off Fall Time	t _f		-	5	-	nS
Total Gate Charge	Qg		-	60	72	nC
Gate-Source Charge	Q _{gs}	$V_{DS}=20V, I_{D}=55A,$	-	9.9		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	9.5		nC
Drain-Source Diode Characteristics			•			
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =55A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	110	Α
Reverse Recovery Time	t _{rr}	T_J = 25°C, I_F = I_S	-		24	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-		68	nC

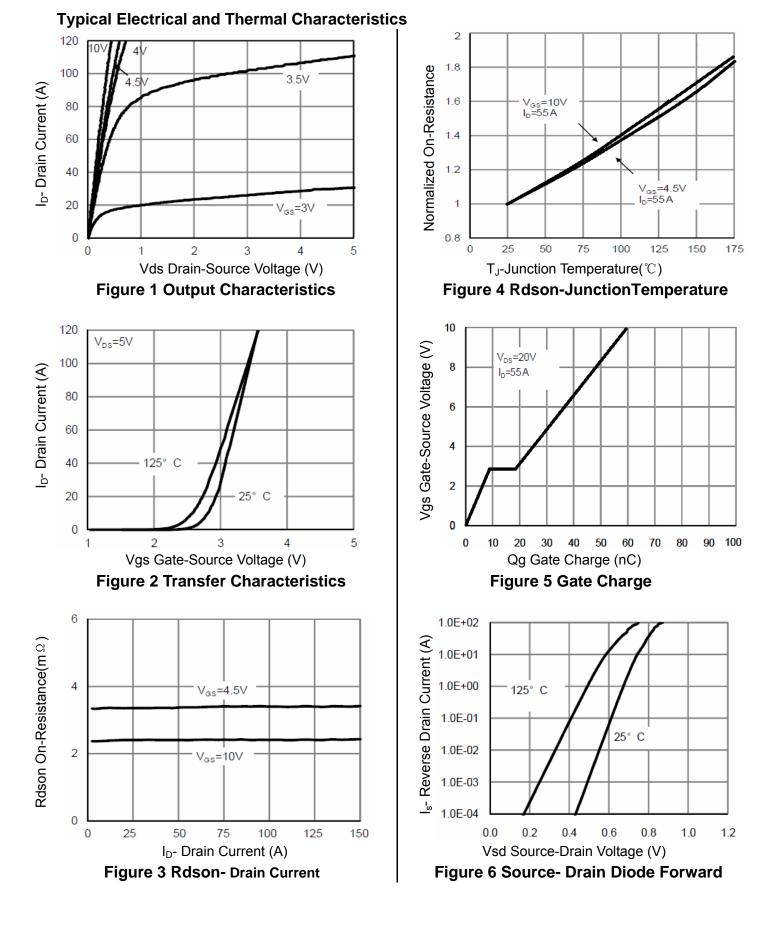
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t \leq 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300 μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^\circ \! \mathrm{C}$,V_DD=20V,V_G=10V,L=0.5mH,Rg=25 Ω





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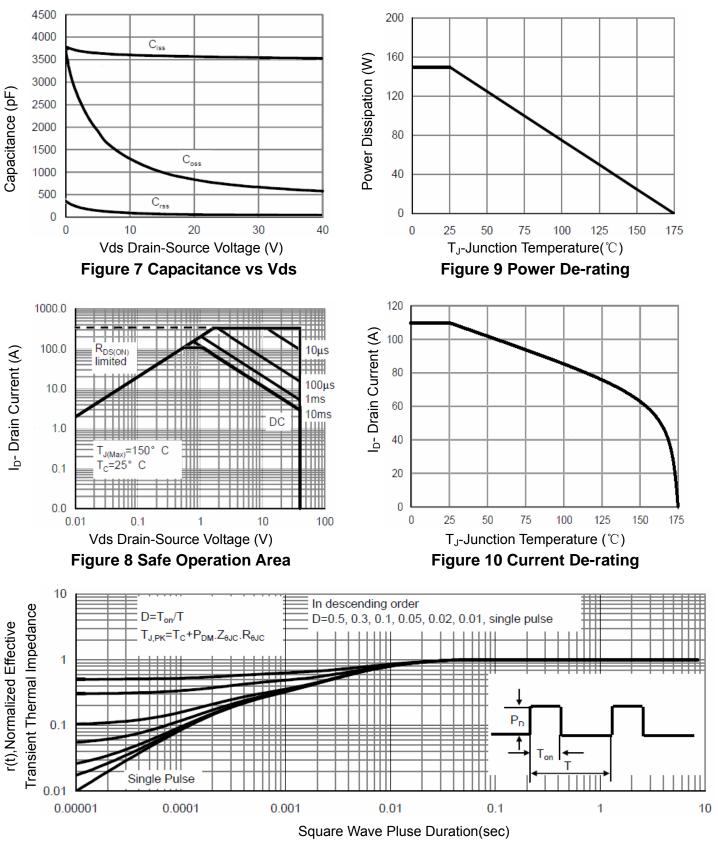


Figure 11 Normalized Maximum Transient Thermal Impedance

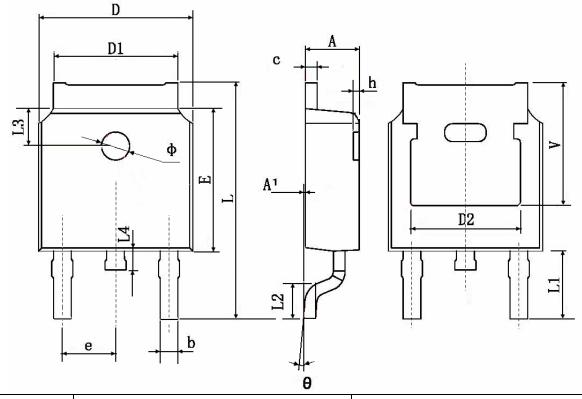


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TO-252-2L Package Information



Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	0.483	TYP.	0.190 TYP.		
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Φ	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350 TYP. 0.211 TYP.			TYP.	







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